Elektronische Bauelemente

2SA1576A

PNP Silicon

Epitaxial Planar Transistor

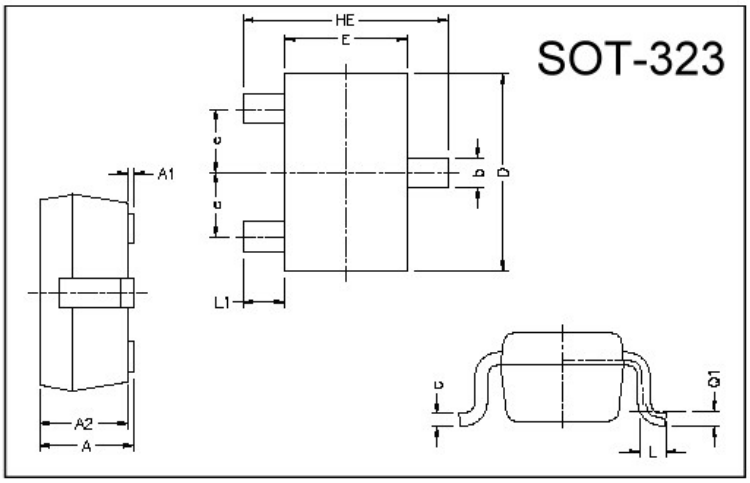
RoHS Compliant Product

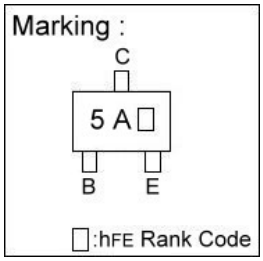
Description

The 2SA1576A is designed for use in driver stage of AF amplifier and general purpose amplificaion.

Feature

*Complements the 2SC4081





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	VCBO	-60	V
Collector to Emitter Voltage	VCEO	-50	V
Emitter to Base Voltage	VEBO	-6	V
Collector Current	IC	-150	mA
Total Power Dissipation	PD	225	mW
Junction and Storage Temperature	Tj, Tstg	-55~+150	℃

Characteristics at Ta = 25℃

Parameter	Symbol	Min	Typ.	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	-60	-	-	V	I_C=-50uA
Collector-Emitter Breakdown Voltage	BV_{CEO}	-50	-	-	V	I_C=-1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-6	-	-	V	I_E=-50uA
Collector-Emitter Breakdown Voltage	I_{CBO}	-	-	-100	nA	V_{CB}=-60V
Emitter-Base Cutoff Current	I_{EBO}	-	-	-100	nA	V_{EB}=-6V
Collector Saturation Voltage	$V_{CE(sat)}$	-	-	-500	mV	I_C=-50mA, I_B=-5 mA
DC Current Gain	h_{FE}	120	-	560	-	V_{CE}=-6V, I_C=-1mA
Gain-Bandwidth Product	fT	-	140	-	MHz	V_{CE}=-12V, I_C=-2mA, f=100MHz
Output Capacitance	Cob	-	4	5	pF	V_{CB}=-12V, f=1MHz, I_E=0

Classification of hFE

Rank	5AQ	5AR	5AS
Range	120 - 270	180 - 390	270 - 560

Characteristics Curve

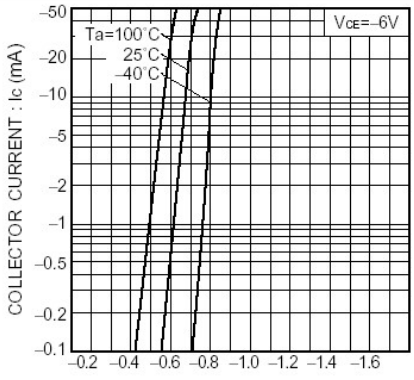


Fig.1 Grounded emitter propagation characteristics

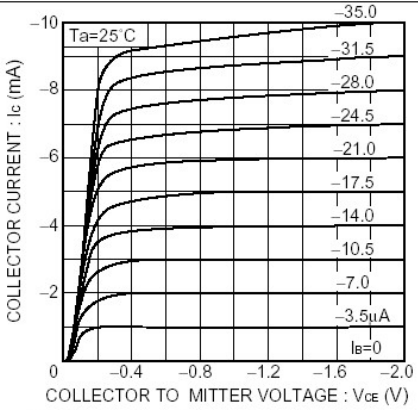


Fig.2 Grounded emitter output characteristics (I)

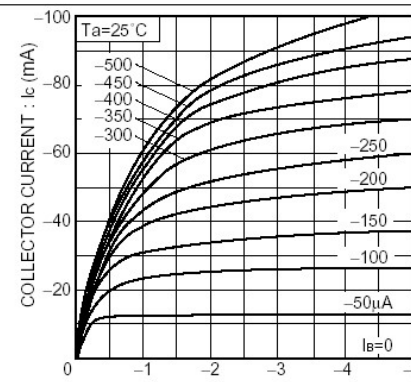


Fig.3 Grounded emitter output characteristics (II)

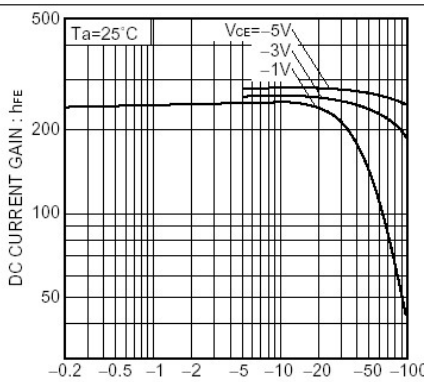


Fig.4 DC current gain vs. collector current (I)

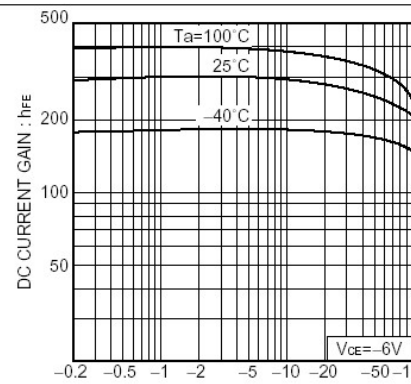


Fig.5 DC current gain vs. collector current (II)

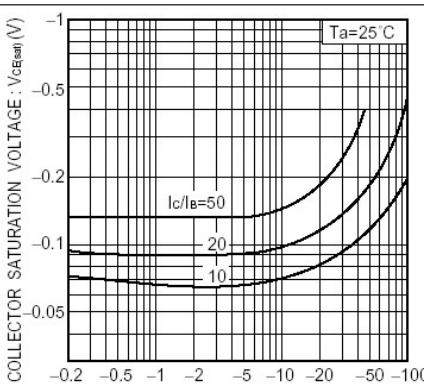


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

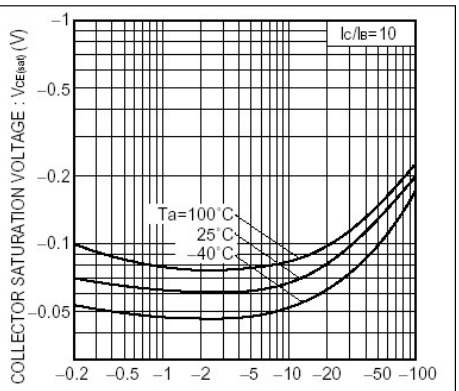


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

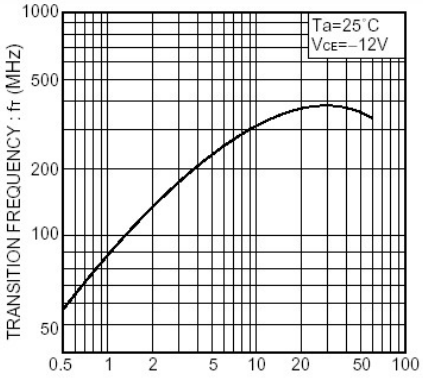


Fig.8 Gain bandwidth product vs. emitter current

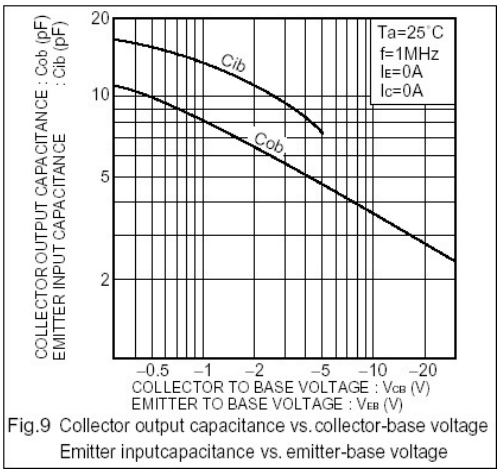


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter inputcapacitance vs. emitter-base voltage